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SJ

**INDUSTRY STANDARD OF THE
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**Semiconductor devices - Discrete components - Test method
for electrical parameters of silicon carbide
metal-oxide-semiconductor field-effect transistors
(English Translation)**

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What this standard covers

This standard specifies general testing methods for silicon carbide metal oxide semiconductor field effect transistors, including rating (limit parameter) verification, electrical characteristic testing and thermal characteristic testing. This standard is applicable to silicon carbide metal oxide semiconductor field effect transistors, and other metal oxide semiconductor field effect transistors can also be used with reference.

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